Radiation-Hardened 8-Channel Level Translator
with **cold sparing**

1 GENERAL DESCRIPTION

The **AF54RHC804** is a radiation-hardened by design **8-channel level translator with 3-state outputs** that is ideally suited for space, medical imaging and other applications demanding radiation tolerance and high reliability. It is fabricated in a 180 nm CMOS process utilizing proprietary radiation-hardening techniques, delivering high resiliency to single-event effects (SEE) and to a total ionizing dose (TID) to **300 krad (Si)**.

This device is a member of the Apogee Semiconductor AF54RHC logic family. All members of this family operate across a full **1.4 V to 5.5 V** range providing the system designer flexibility in logic-level interfaces. The AF54RHC804 can operate across this range on both of its supply voltage inputs, V_{CC}A and V_{CC}Y.

An output enable control pin allows the outputs to be placed in a high impedance (high-Z) state, simplifying usage in applications with shared busses or mixed power domains. Additionally, the outputs are placed in high-Z when V_{CC}A or V_{CC}Y is not present, ensuring that no loading or leakage paths are experienced at the output nodes when the input rail is not powered.

Zero-power penalty™ cold sparing is supported, along with Class 1C ESD protection on all inputs and outputs. A proprietary output stage and robust power-on reset (POR) circuit allow the AF54RHC804 to be cold-spared in any redundant configuration with no static power loss on any pad of the device. The redundant output stage also features a high drive capability with low static power loss.

The AF54RHC804 also features a triple-redundant design throughout its entire circuitry, which allows it to be immune to single-event transients (SET) without requiring additional redundant devices.

Ordering information may be found in Table 10 on Page 15.

1.1 FEATURES

- **1.4 VDC to 5.5 VDC** operation
- Inputs tolerant up to 5.5 VDC at any V_{CC}A
- Provides logic-level translation to V_{CC}Y
- Extended operating temperature range (-55 °C to +125 °C)
- Proprietary **cold sparing capability** with **zero** static power penalty
- **Built-in triple redundancy** for enhanced reliability
- Tri-state output drivers
- Class 1C ESD protection (1000 V HBM, 500 V CDM)
- TID resilience of **300 krad (Si)**.
- SEL immune to LET of **75 MeV-cm^2/mg**
- Meets NASA's ASTM E595 outgassing specification

1.2 LOGIC DIAGRAM

The AF54RHC804 logic function is shown below:

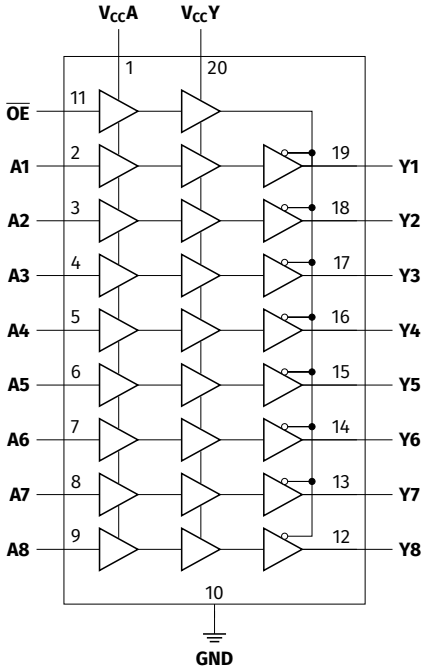


Figure 1: AF54RHC804 Logic Diagram

CONTENTS

LIST OF TABLES

LIST OF FIGURES

2 ACRONYMS AND ABBREVIATIONS

ESD	Electrostatic Discharge
POR	Power On Reset
RHA	Radiation Hardness Assurance
SEE	Single Event Effects
SEL	Single Event Latchup
SET	Single Event Transient
TID	Total Ionizing Dose
TMR	Triple Modular Redundancy
CDM	Charged-device Model
HBM	Human-body Model

3 LOGIC DATA

The AF54RHC804 truth table is found in Table 1. **H** indicates HIGH logic level, **L** indicates LOW logic level, **X** indicates DON'T CARE and **Z** indicates HIGH-Z (TRI-STATE). Subscript **n** reflects one of the eight buffers in the device (1 to 8).

Table 1: AF54RHC804 Device Truth Table

Inputs		Output
$\overline{OE}$	A_n	Y_n
L	L	L
L	H	H
H	X	Z

4 PIN CONFIGURATION

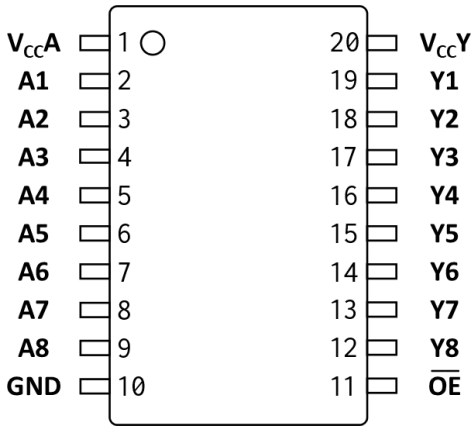


Figure 2: AF54RHC804 Device Pinout

Table 2: AF54RHC804 Device Pinout

PIN NAME(S)	PIN NUMBER(S)	DESCRIPTION
A1 A2 A3 A4 A5 A6 A7 A8	2 3 4 5 6 7 8 9	Signal Inputs. Referenced to $V_{CC}A$.
Y1 Y2 Y3 Y4 Y5 Y6 Y7 Y8	19 18 17 16 15 14 13 12	Signal Outputs. Referenced to $V_{CC}Y$.
$\overline{OE}$	11	Output Enable (active-low). Referenced to $V_{CC}A$.
$V_{CC}A$	1	Positive Voltage Supply (A Side)
$V_{CC}Y$	20	Positive Voltage Supply (Y Side)
GND	10	Ground

5 ELECTRICAL CHARACTERISTICS

The sign convention for current follows JEDEC standards with negative values representing current sourced from the device and positive values representing current sunk into the device.

5.1 ABSOLUTE MAXIMUM RATINGS

Excursions beyond the values listed in Table 3 may cause permanent damage to the device. Proper function of the device cannot be guaranteed if these values are exceeded, and long-term device reliability may be affected. Functionality of the device at these values, or beyond those listed in Recommended Operating Conditions (Table 4) is not guaranteed.

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 3: Absolute Maximum Ratings

SYMBOL	PARAMETER		VALUE	UNITS
$V_{CC}A$, $V_{CC}Y$	Supply Voltage		-0.5 to +5.5	V
V_I	Input voltage range		-0.5 to +5.5	V
V_O	Output voltage range		-0.5 to + 5.5	V
I_{IK} (V_I < 0)	Input clamp current		100	mA
I_O	Continuous output current (per pin)		100	mA
I_{CC}	Maximum supply current		100	mA
V_{ESD}	ESD Voltage	HBM	1000	V
		CDM	500	V
T_J	Operating junction temperature range		-55 to +150	°C
T_{STG}	Storage temperature range		-65 to +150	°C

5.2 RECOMMENDED OPERATING CONDITIONS

All recommended parameters below are specified across the entire operating temperature range unless otherwise specified.

Table 4: Recommended Operating Conditions

SYMBOL	PARAMETER		MIN	MAX	UNITS
$V_{CC}A$, $V_{CC}Y$	Supply voltage		1.4	5.5	V
V_I	Input voltage range		0	5.5	V
V_O	Output voltage range		0	$V_{CC}Y$	V
V_{IH}	HIGH-level input voltage	$V_{CC}A$ = 1.4 to 1.6 V	1.12	-	V
		$V_{CC}A$ = 1.65 to 1.95 V	1.4	-	
		$V_{CC}A$ = 2.3 to 2.7 V	1.9	-	
		$V_{CC}A$ = 3.0 to 3.6 V	2.5	-	
		$V_{CC}A$ = 4.5 to 5.5 V	3.8	-	
V_{IL}	LOW-level input voltage	$V_{CC}A$ = 1.4 to 1.6 V	-	0.32	V
		$V_{CC}A$ = 1.65 to 1.95 V	-	0.4	
		$V_{CC}A$ = 2.3 to 2.7 V	-	0.6	
		$V_{CC}A$ = 3.0 to 3.6 V	-	0.9	
		$V_{CC}A$ = 4.5 to 5.5 V	-	1.35	
I_{OH}	HIGH-level output current	$V_{CC}Y$ = 1.4 to 1.6 V	-	-2	mA
		$V_{CC}Y$ = 1.65 to 1.95 V	-	-4	
		$V_{CC}Y$ = 2.3 to 2.7 V	-	-8	
		$V_{CC}Y$ = 3.0 to 3.6 V	-	-16	
		$V_{CC}Y$ = 4.5 to 5.5 V	-	-24	
I_{OL}	LOW-level output current	$V_{CC}Y$ = 1.4 to 1.6 V	-	2	mA
		$V_{CC}Y$ = 1.65 to 1.95 V	-	4	
		$V_{CC}Y$ = 2.3 to 2.7 V	-	8	
		$V_{CC}Y$ = 3.0 to 3.6 V	-	16	
		$V_{CC}Y$ = 4.5 to 5.5 V	-	24	
t_r, t_f	Input rise or fall time (10% - 90%)	$V_{CC}A$ = 1.4 to 1.6 V	-	2000	ns
		$V_{CC}A$ = 1.65 to 1.95 V	-	1000	
		$V_{CC}A$ = 2.3 to 2.7 V	-	600	
		$V_{CC}A$ = 3.0 to 3.6 V	-	500	
		$V_{CC}A$ = 4.5 to 5.5 V	-	400	

Table 5: Thermal Information

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
T_J	Operating junction temperature	-55	-	+125	°C
$R_{\theta JA}$	Junction to ambient thermal resistance	-	100	-	°C/W

5.3 STATIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 6: DC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	$V_{CC}Y$	MIN	TYP	MAX	UNITS
V_{OL}	LOW-Level Output Voltage(1)	I_O = 100 µA	1.4 to 5.5 V	-	0.02	0.05	V
		I_O = 1 mA	1.4 to 5.5 V	-	0.05	0.15	V
		I_O = 2 mA	1.4 V	-	0.18	0.4	V
		I_O = 4 mA	1.65 V	-	0.27	0.8	V
			2.3 V	-	0.3	0.6	V
			3.0 V	-	0.2	0.4	V
			4.5 V	-	0.2	0.4	V
		I_O = 8 mA	2.3 V	-	0.6	1.0	V
			3.0 V	-	0.4	0.8	V
			4.5 V	-	0.3	0.6	V
		I_O = 16 mA	3.0 V	-	1.0	1.4	V
			4.5 V	-	1.1	1.2	V
		I_O = 24 mA	4.5 V	-	1.1	1.5	V
V_{OH}	HIGH-Level Output Voltage(1)	I_O = -100 µA	1.4 to 5.5 V	$V_{CC}Y$ - 0.1	$V_{CC}Y$ - 0.02	-	V
		I_O = -1 mA	1.4 to 5.5 V	$V_{CC}Y$ - 0.15	$V_{CC}Y$ - 0.08	-	V
		I_O = -2 mA	1.4 V	0.9	1.2	-	V
		I_O = -4 mA	1.65 V	1	1.35	-	V
			2.3 V	1.8	2.0	-	V
			3.0 V	2.6	2.7	-	V
			4.5 V	4.2	4.4	-	V
		I_O = -8 mA	2.3 V	1.4	1.7	-	V
			3.0 V	2.2	2.5	-	V
			4.5 V	3.9	4.1	-	V
		I_O = -16 mA	3.0 V	1.5	2.0	-	V
			4.5 V	3.3	3.8	-	V
		I_O = -24 mA	4.5 V	3.0	3.5	-	V
$I_{CC}Y$	Quiescent supply current	V_I = $V_{CC}A$ or GND $\overline{OE}$ = GND I_O = 0 mA	5.5 V	-	75	200	µA
SYMBOL	**PARAMETER**	**CONDITIONS**	**$V_{CC}A$**	**MIN**	**TYP**	**MAX**	**UNITS**
I_I	Input current	V_I = $V_{CC}A$ or GND	1.4 to 5.5 V	-	-	±8	µA
I_{OZ}	Output leakage current(2)	V_I = $V_{CC}Y$ or GND $\overline{OE}$ = $V_{CC}A$	1.4 to 5.5 V	-	-	±2.5	µA
I_{OFF}	Powerdown leakage current(2, 3)	V_I = GND to 5.5 V	OFF	-	-	8	µA
$I_{CC}A$	Quiescent supply current	V_I = $V_{CC}A$ or GND I_O = 0 mA	5.5 V	-	30	100	µA

(1) $V_{CC}A$ = 1.4 to 5.5 V for these conditions
(2) $V_{CC}Y$ = 0 to 5.5 V for these conditions
(3) $V_{CC}A$ is at GND potential

5.4 DYNAMIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 7: AC Electrical Characteristics. C_L = 50 pF

Symbol	Parameter	V_{CC}A	V_{CC}Y 1.5 ±0.1 V		V_{CC}Y 1.8 ±0.15 V		V_{CC}Y 2.5 ±0.2 V		V_{CC}Y 3.3 ±0.3 V		V_{CC}Y 5 ±0.5 V		Units
			TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	TYP	MAX	
t_{pd}[1]	Propagation Delay (Input **A** to Output **Y**)	1.5 ±0.1 V	24.5	60	15.6	41	10.6	23	8.9	20	8.2	18	ns
		1.8 ±0.15 V	18.5	60	11.8	25	7.9	15	6.2	13	5.8	11	ns
		2.5 ±0.2 V	18	60	11.3	25	7.4	15	5.6	13	4.3	11	ns
		3.3 ±0.3 V	17.8	60	11.2	25	7.2	15	5.4	13	4.2	11	ns
		5 ±0.5 V	17.7	60	11.1	25	7.1	15	5.3	13	3.9	11	ns
t_{dis}[2]	Output Disable Time (Input $\overline{\textbf{OE}}$ to Output **Y**)	1.5 ±0.1 V	30.1	45	25.9	40	22.6	37	21.8	35	21.8	33	ns
		1.8 ±0.15 V	27.3	80	18.3	53	17.2	41	17.1	35	18.2	25	ns
		2.5 ±0.2 V	26.8	80	17.9	53	16.7	41	16.3	35	16.2	25	ns
		3.3 ±0.3 V	26.1	80	17.7	53	16.6	41	16.1	35	15.9	25	ns
		5 ±0.5 V	26	80	17.7	53	16.5	41	16.1	35	15.9	25	ns
t_{en}[3]	Output Enable Time (Input $\overline{\textbf{OE}}$ to Output **Y**)	1.5 ±0.1 V	56.5	91	38.6	69	24.4	42	20.9	36	19.3	31	ns
		1.8 ±0.15 V	47	80	21.7	53	17.3	41	15.5	35	15.1	25	ns
		2.5 ±0.2 V	46.5	80	21.4	53	16.9	41	15.0	35	13.7	25	ns
		3.3 ±0.3 V	46.3	80	21.3	53	16.8	41	14.9	35	13.5	25	ns
		5 ±0.5 V	46.4	80	21.4	53	17.0	41	15.0	35	13.6	25	ns

(1) equivalent to t_{PLH}, t_{PHL}
(2) equivalent to t_{PLZ}, t_{PHZ}
(3) equivalent to t_{PZL}, t_{PZH}

Table 8: AC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V_{CC}Y	MIN	TYP	MAX	UNITS
t_{sk}	Channel-to-channel skew[1]	C_L = 50 pF	1.4 to 5.5 V	-	-	1	ns
C_{in}	Input Capacitance[1]	V_I = V_{CC} or GND	1.4 to 5.5 V	-	2	4	pF
C_{pd}	Power Dissipation Capacitance[1]	I_O = 0 mA, f = 1 MHz	5.5 V	-	40	-	pF

(1) guaranteed by design

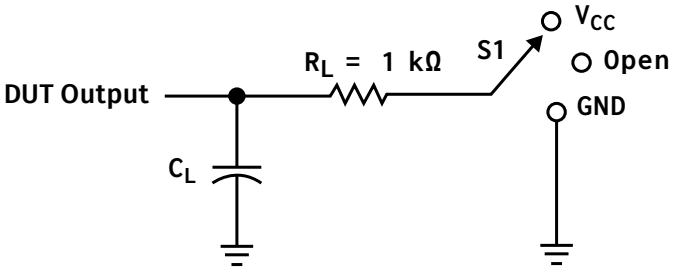
5.5 RADIATION RESILIENCE

For detailed radiation testing reports, please contact Apogee Semiconductor at sales@apogeesemi.com.

Table 9: Radiation Resilience Characteristics

PARAMETER	CONDITIONS	VALUE	UNITS
Total Ionizing Dose (TID)	Please contact Apogee Semiconductor for test report.	300	krad (Si)
SEL Onset LET Threshold	Please contact Apogee Semiconductor for test report.	≥75	MeV-cm^2/mg

5.6 CHARACTERISTICS MEASUREMENT INFORMATION



TEST	S1
t_{pd}	GND
t_{PLZ}, t_{PZL}	V_{CC}
t_{PHZ}, t_{PZH}	GND

Figure 3: Load Circuit for 3-State Outputs

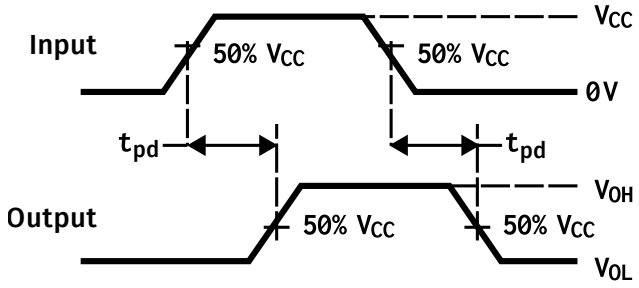


Figure 4: Propagation Delay Measurement

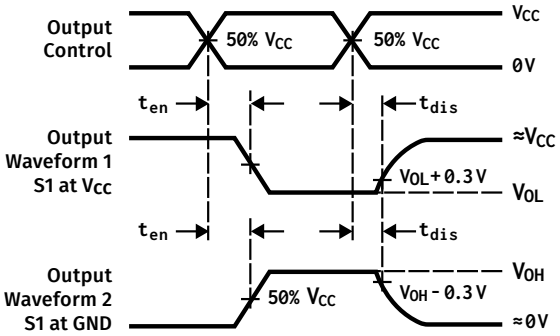


Figure 5: Enable and Disable Time Measurements

6 DETAILED DESCRIPTION

The AF54RHC804 is a 8-channel level translator with 3-state outputs designed to operate from a wide supply voltage of 1.4 to 5.5 V with fully redundant input and output stages, providing for superior radiation resilience.

The output and input stages are constructed with transient-activated clamps (Figure 6, 7) that prevent inadvertent biasing of the V_{CC} power rail through parasitic diodes inherent to conventional input, output, and ESD circuits. The IC also incorporates an internal power-on reset (POR) circuit guaranteeing correct operation at power supply voltages as low as 1.4V.

The AF54RHC family's I/O protection circuitry allows for cold sparing configurations as it avoids a leakage current penalty on inputs and outputs while in a power-down state. This can result in considerable power savings in systems where multiple-path redundancy is employed. The ESD clamp circuits for this logic family are designed to support Class 1C ESD levels of 1 kV HBM and 500 V CDM.

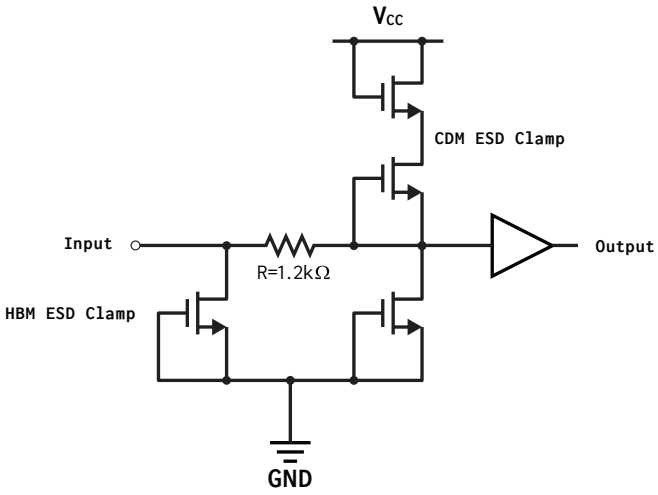


Figure 6: Input Pin Structure

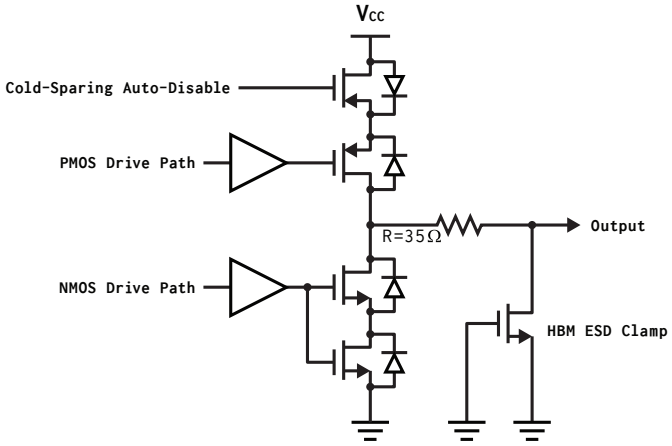


Figure 7: Output Pin Structure

7 APPLICATIONS INFORMATION

The AF54RHC804 provides a simple and robust means of interfacing digital logic between different voltage levels and domains. It can shift logic signals up from a lower voltage to a higher voltage or shift signals down from higher to lower voltages.

It offers several features that make interfacing between different domains simple. First, the absence of an input supply voltage results in a tri-state condition at the output. Second, the outputs may also be tri-stated through assertion of the $\overline{OE}$ pin, which can be tied with power-supply enables or other control signals.

In an application utilizing a modern FPGA with 1.5 V I/O buffers that needs to interface to systems running at higher voltages (i.e. 5 V), the AF54RHC804 can be used to shift these signals to a range appropriate for the FPGA. The AF54RHC804 provides integrated triple modular redundancy (TMR), as well as SET resiliency on each buffer. In the event the 5 V supply is off, the AF54RHC804 will automaticaly tri-state the output buffers. The $\overline{OE}$ pin of the device can be tied to the FPGA power-enable logic such that $\overline{OE}$ is de-asserted when the 1.5 V I/O rail is not present. Figure 8 shows an example of a Versal FPGA utilizing two AF54RHC804 and a AF54RHC301 majority voter to add additional redundancy for critical control and telemetry signals with error feedback. See the AF54RHC301 product folder

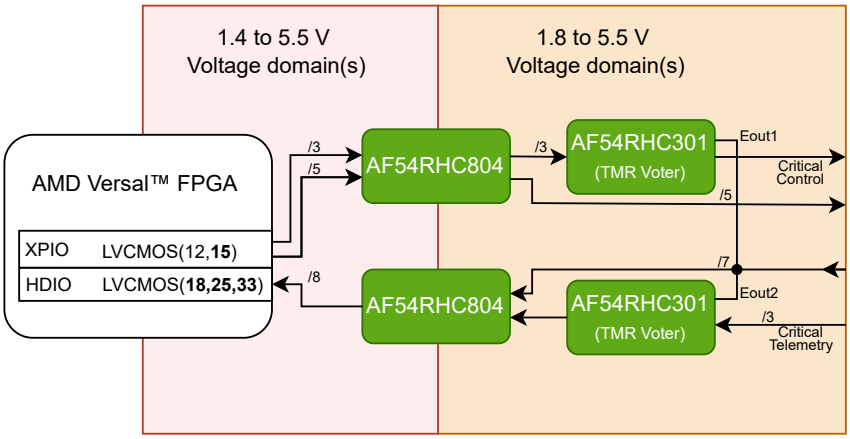
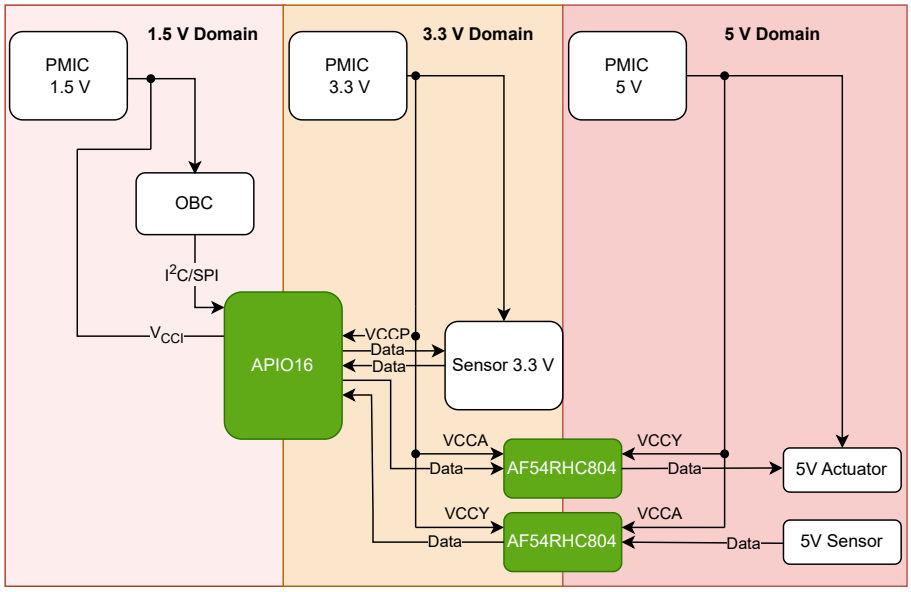


Figure 8: Level Shifting utilizing AF54RHC804

Figure 9 shows a multi-domain level shifting application using AF54RHC804 and an AFIO16 radiation hardened I/O expander. In this configuration, the AFIO16 is used to level shift to and from the low voltage 1.5 V domain to the 3.3 V domain. The AF54RHC804s are used to level shift to and from the 3.3 V domain to the 5 V domain. The AFIO16 provides 16 additional input or output channels that can be used to expand the I/O capabilities of the a processor or FPGA with limited I/O resources. It can be controlled via a simple I^2C or SPI interface. See the AFIO16 product folder for more information.



a

Figure 9: Multi DomainLevel Shifting using AF54RHC804 and AFIO16

7.1 APPLICATIONS EXAMPLE

As the AF54RHC family is radiation-hardened by design and includes internal TMR, it can be utilized in high-reliablity applications without additional supporting circuitry or devices. Nonetheless, some application requirements call for fully-redundant designs, where an “A” and a “B” device are required, often on separate power rails.

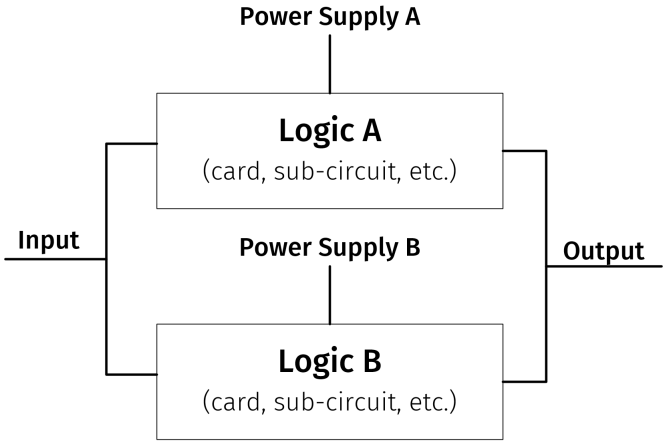


Figure 10: Two-Path Cold-Sparing Configuration

With the cold sparing capability of the AF54RHC family, fully redundant “A” and “B” functions may be placed in parallel (as seen in Figure 10) running off redundant power supplies. The inputs and outputs on each one of these functions are assumed to be based on the AF54RHC family, allowing for direct parallel connection without unwanted leakage current paths during cold sparing. In the event of a failure in power supply A or within function A, the system can simply shut power supply A off and switch on power supply B, without requiring additional input or output switching or configuration changes.

7.2 POWER SUPPLY RECOMMENDATIONS

This device can operate at any voltage within the range specified in Table 4 Recommended Operating Conditions.

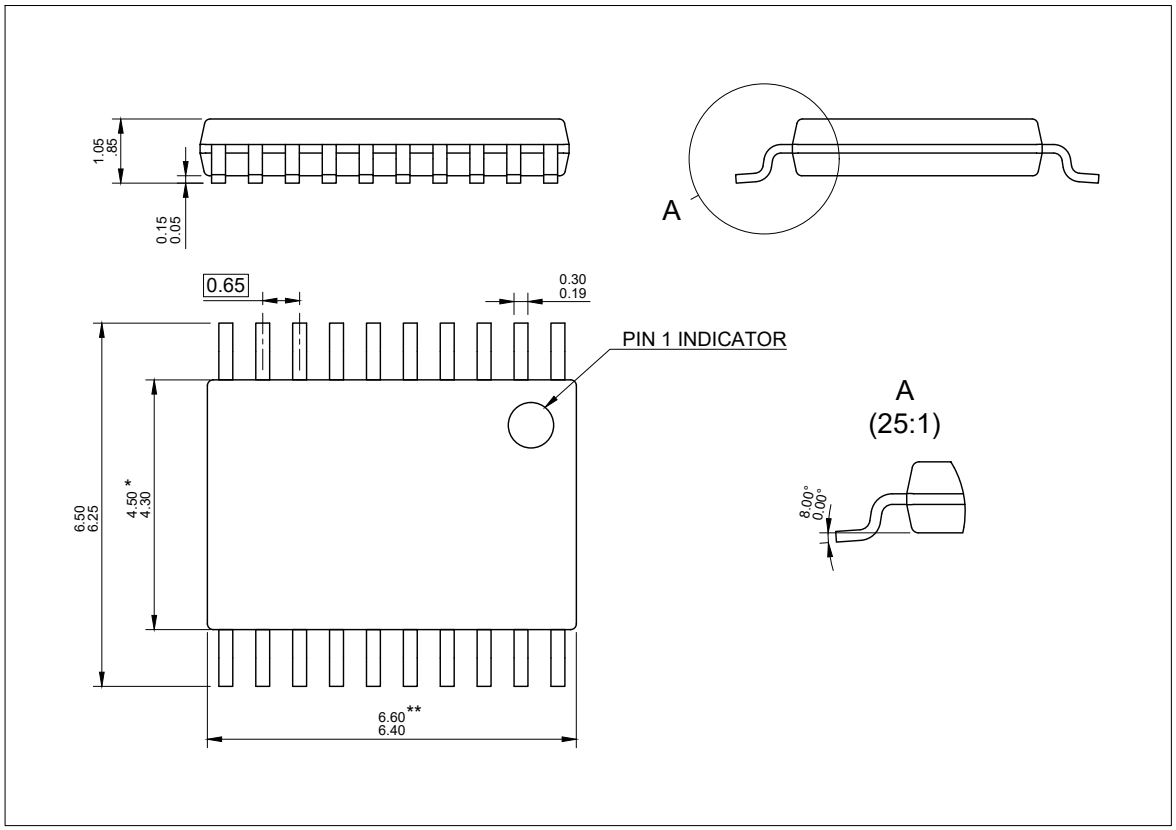
At a minimum, a 16 VDC (or higher), X7R-rated 0.1 µF ceramic decoupling capacitor should be placed near (within 1 cm) the V_{CC} pins of the device.

7.3 APPLICATION TIPS

Unused **inputs** must **not** be left floating. They may be connected to either a low (GND) or high (V_{CC}A) bias to provide a known state at the input of the device. Resistors may be used to tie off unused inputs. In the event of a design change, such resistors can be removed, thereby allowing use of the inputs without having to cut traces on the PCB.

An unused **output** may be left floating. It is suggested that it be routed to a test point or similar accessible structure in case the associated function needs to be utilized as part of a design revision.

8 PACKAGING INFORMATION



Notes:
1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010
2. The part is compliant with JEDEC MO-153 specifications.

* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side.
** Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

Figure 11: Package Mechanical Drawing

9 ORDERING INFORMATION

Example part numbers for the AF54RHC804 are listed in Table 10. The full list of options for this part can be found in Figure 12. For a detailed description of product grades, please refer to Product Grades and Quality Flows document. Please contact Apogee Semiconductor sales at sales@apogeesemi.com for further information on sampling, lead time and purchasing on specific part numbers.

Table 10: AF54RHC804 Ordering Information

DEVICE	DESCRIPTION	PACKAGE	LEAD FINISH	PACKAGE MASS
AF54RHC804ANT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ANT-J(1)	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804BNT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804BNT-J(1)	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804CNT-R	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804CNT-J(1)	Rad-Hard 8-Channel Level Translator (300 krad (Si))	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ENT-R	Rad-Hard 8-Channel Level Translator (for eval only)	Plastic TSSOP-20	NiPdAu	73.7 mg
AF54RHC804ENT-J(1)	Rad-Hard 8-Channel Level Translator (for eval only)	Plastic TSSOP-20	NiPdAu	73.7 mg

(1) Available through distributors only.

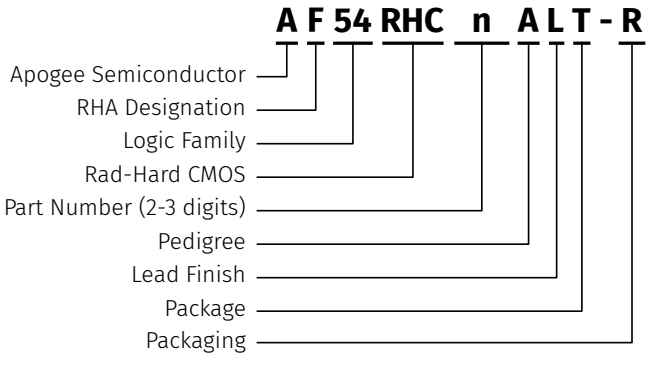


Figure 12: Part Number Decoder

1. RHA Designation
   - **P** 30 krad (Si)
   - **F** 300 krad (Si)
2. Part Number
   - **_** 804 (8-Channel Level Translator)
3. Pedigree
   - **A** -55 to +125 °C (Burn-in)
   - **B** -55 to +125 °C (No burn-in)
   - **C** 25 °C (No burn-in)
   - **E** 25 °C Functional Test Only (Evaluation)
4. Lead Finish
   - **N** Nickel-Palladium-Gold (NiPdAu)
5. Package
   - **T** 20-pin Thin Shrink Small Outline Package (TSSOP)
6. Packaging
   - **R** Tape and Reel(1)
   - **J** JEDEC Tray

(1) Contact us for custom reel quantities. Orders less than full reel quantities may be shipped as cut tape.

10 REVISION HISTORY

REVISION	DESCRIPTION	DATE
C03	Add note for Tsk parameter to be guaranteed by design. Relaxed Vo Absolute Maximum Rating. Updated Applications section.	2025-12-18
C02	For $V_{CC}A$ = 1.4 to 1.6 V, V_{IH} limit corrected from 0.6 V to 1.12 V and V_{IL} limit corrected from 0.25 V to 0.32 V. Timing parameters t_{pd}, t_{en}, and t_{dis} updated in Table 7 for $V_{CC}A$ = 1.5 ±0.1 V.	2025-10-31
C01	SEL onset threshold was corrected from ≥80 MeV-cm^2/mg to ≥75 MeV-cm^2/mg.	2025-08-28
C00	Initial release	2025-08-19

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